

L Number	Hits	Search Text	DB	Time stamp
1	98263	((field adj effect adj transistor) fet mosfet) and (method process)	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:42
2	21417	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:43
3	7747	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:46
4	606	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k")	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:46
5	671	((high near1 dielectric near1 constant) "high-k") with (hafnium zirconium hfo zro)	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:49
6	787	((high adj1 dielectric) "high-k") with (hafnium zirconium hfo zro)	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:00
7	91	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k") with (hafnium zirconium hfo zro))	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:57
8	0	oxygen near1 attracting near1 layer	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:58
10	0	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k") with (hafnium zirconium hfo zro))) and (oxygen near1 (attracting attracted))	USPAT; US-PGPUB; EPO; JPO	2004/07/09 15:58
11	26651	((high adj1 dielectric) "high-k")	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:01
12	606	((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k"))	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:01
13	0	(oxygen near1 (attracting attracted)) and ((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k")))	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:08
9	81	oxygen near1 (attracting attracted)	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:01

14	606	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k"))))	USPAT; US-PGPUB; EPO; JPO	2004/07/09 16:08
-	204407	(field adj effect adj transistor) fet mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 09:17
-	109613	((field adj effect adj transistor) fet mosfet) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:42
-	21196	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:43
-	7537	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:45
-	460	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near region)) and ((high near1 dielectric near1 constant) "high-k")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:46
-	669	((high near1 dielectric near1 constant) "high-k") with (hafnium zirconium hfo zro)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/09 15:48
-	121	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and ((high near1 dielectric near1 constant) "high-k") with (hafnium zirconium hfo zro))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 09:23